

Docket No.: 50090-318

#8/Amend B
Patent
7/31/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



re Application of

Shifumi TAKATA, et al.

Serial No.: 09/903,760

Filed: July 13, 2001

Group Art Unit: 2822

Examiner: J. Mitchell

For: SEMICONDUCTOR DEVICE HAVING AN IMPROVED INTERLAYER
CONDUCTOR CONNECTIONS AND A MANUFACTURING METHOD
THEREOF

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AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in reponse to the Office

Action dated April 19, 2002.

IN THE CLAIMS:

Please amend claim 9 as follows.

9. (Amended) A method of manufacturing a semiconductor device
comprising the steps of:

forming a first interlayer insulating film on a semiconductor substrate;

forming a plurality of openings in said first interlayer insulating film;

forming a conductor film on said first interlayer insulating film so as to fill said

openings;